

Substitute for form 1449A/PTO

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PTO/SB/08A(10-01)
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US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	08/903453
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Gr up Art Unit	2815
Examiner Name	Eckert II, George

Sheet 1 of 1

Attorney Docket No: 00303.378US1

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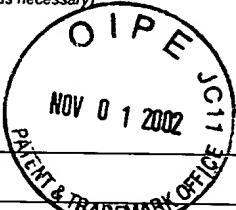
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Substitute Disclosure Statement Form (PTO-1449)
 * EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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